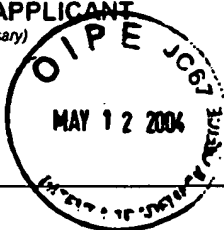


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Application Number	10/623788
Filing Date	July 21, 2003
First Named Inventor	Forbes, Leonard
Group Art Unit	2811
Examiner Name	Unknown

Sheet 1 of 7

Attorney Docket No: 1303.109US1

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	Application Number	10/623788
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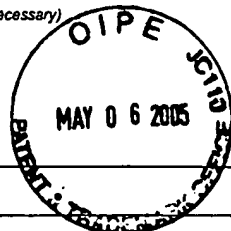
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Application Number	10/623,788
Filing Date	July 21, 2003
First Named Inventor	Forbes, Leonard
Group Art Unit	2811
Examiner Name	Unknown

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	Application Number	10/623,788
	Filing Date	July 21, 2003
	First Named Inventor	Forbes, Leonard
	Group Art Unit	2811
	Examiner Name	Unknown
Sheet 2 of 2	Attorney Docket No: 1303.109US1	

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Examiner Initials*	Cite No. <sup>1</sup>	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T <sup>2</sup>
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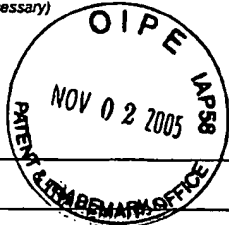
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Application Number	10/623,788
Filing Date	July 21, 2003
First Named Inventor	Forbes, Leonard
Group Art Unit	2822
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